

## EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	1398	257/368.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/19 17:55
S1	519	FINFET or (fin adj field adj effect adj transistor)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/01 13:29
S2	13	S1 and ((source or drain) with Schottky with channel)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/31 18:13
S3	9	S2 and (Schottky with (platinum adj silicide) or (platinum adj germanium adj silicide) or (erbium adj silicide) or PtSi or PtGeSi or ErSi)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/01 17:02
S4	6	S3 and (gate with spacer)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/31 17:06
S5	3	S4 and (gate with (oxide and nitride))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/31 17:04
S6	1	"6198113".PN.	USPAT; USOCR	OR	ON	2005/08/31 17:18
S7	1	"5801398".PN.	USPAT; USOCR	OR	ON	2005/08/31 17:19
S8	1	"5021365".PN.	USPAT; USOCR	OR	ON	2005/08/31 17:20
S9	1	"3983264".PN.	USPAT; USOCR	OR	ON	2005/08/31 17:20
S10	1318	257/368.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/19 17:55

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S11	768	257/382.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/31 18:14
S12	463	(raised adj channel)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/01 12:43
S13	0	S12 and FINFET	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/01 12:43
S14	1009	(raised adj (source or drain))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/01 12:44
S15	49	S14 and FINFET	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/01 12:52
S16	0	S15 and ((diffusion adj barrier) with (source or drain) with channel)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/01 13:34
S17	5	S15 and (diffusion adj barrier)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/01 12:53
S18	521	FINFET or (fin adj field adj effect adj transistor)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/01 13:29
S19	2	S18 and ((diffusion adj barrier) with (source or drain) with channel)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/01 13:31
S20	0	257/368.clm. and ((diffusion adj barrier) with (source or drain) with channel)	US-PGPUB	OR	ON	2005/09/01 13:32

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S21	89	((diffusion adj barrier) with (source or drain) with channel)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/01 13:45
S22	14	S21 and schottky	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/01 13:35
S23	3	((diffusion adj barrier) with schottky with (source or drain) with channel)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/01 13:37
S24	2	"20010036693"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/01 17:00
S25	0	S24 and fin	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/01 16:59
S26	0	S24 and finfet	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/01 16:59
S27	0	S24 and (Schottky with (platinum adj silicide) or (platinum adj germanium adj silicide) or (erbium adj silicide) or PtSi or PtGeSi or ErSi)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/01 17:05
S28	0	S24 and Schottky	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/01 17:03
S29	1532	S24 and (platinum adj silicide) or (platinum adj germanium adj silicide) or (erbium adj silicide) or PtSi or PtGeSi or ErSi	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/01 17:05
S30	0	S24 and ((platinum adj silicide) or (platinum adj germanium adj silicide) or (erbium adj silicide) or PtSi or PtGeSi or ErSi)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/01 17:05

## EAST Search History

S31	2	"20010036693"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/14 14:28
S32	1	fin with (MOS or FET) with (SOI or (insulating adj substrate)) with raised with (source or drain)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/14 14:32
S33	2	fin with (SOI or (insulating adj substrate)) with raised with (source or drain)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/14 14:32
S34	303	fin with (SOI or (insulating adj substrate))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/14 14:32
S35	58	fin with (MOS or FET) with (SOI or (insulating adj substrate))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/14 14:32